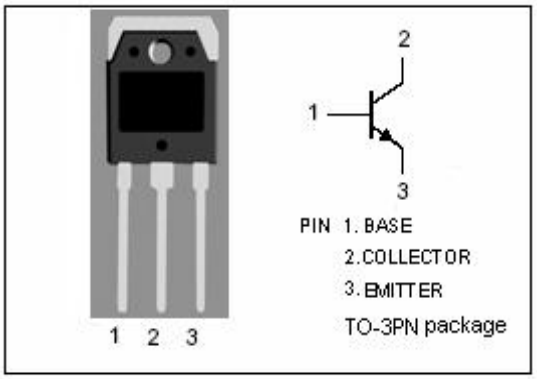
isc Silicon NPN Power Transistor — 2SC3256



DESCRIPTION

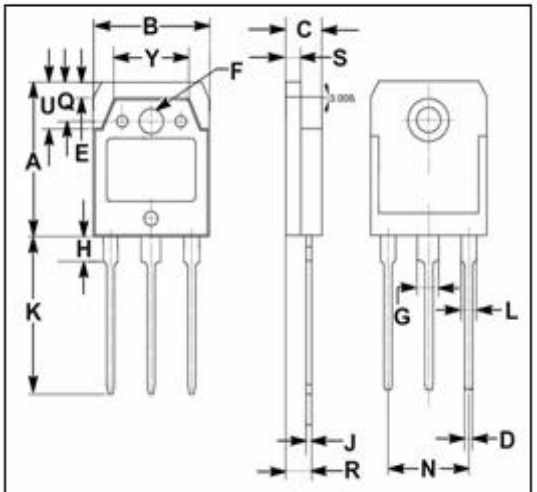
- Low Collector Saturation Voltage
- Good Linearity of h_{FE}
- High Switching Speed
- Complement to Type 2SA1292
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Various inductance lamp drivers for electrical equipment
- Inverters, converters
- Power amplifier
- Switching regulator, dirver

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	15	A
I_{CM}	Collector Current-Pulse	20	A
P_C	Collector Power Dissipation @ T_C=25℃	80	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	19.60	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	20.00	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.10
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 1mA ; R_{BE}= ∞	60			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 1mA; I_E= 0	80			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA; I_C= 0	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 7.5A; I_B= 0.375A			0.4	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 40V; I_E= 0			100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 4V; I_C= 0			100	μA
h_{FE}	DC Current Gain	I_C= 1A; V_{CE}= 2V	70		280	
f_T	Current-Gain—Bandwidth Product	I_C=1A; V_{CE}= 5V		100		MHz
Switching times						
t_{on}	Turn-on Time	I_C= 6A; I_{B1}= -I_{B2}= 0.3A; R_L= 3.3Ω ; V_{CC}= 20V		0.1		μs
t_{stg}	Storage Time			0.5		μs
t_f	Fall Time			0.1		μs

◆ **h_{FE} Classifications**

Q	R	S
70-140	100-200	140-280